

INFORMATION DISCLOSURE STATEMENT BY APPLICANT				ATTY. DOCKET NO. 061282-0234		SERIAL NO. 10/574,863	
				APPLICANT Yuichiro SASAKI, et al.			
(Substitute for form 1449/PTO)				FILING DATE April 06, 2006		GROUP 2823	
				U.S. PATENT DOCUMENTS			
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
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EXAMINER /George Fournon/			DATE CONSIDERED 03/11/2010				

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1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

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